NSN 5962-01-374-2366

Memory Microcircuit - Page 1 of 1



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O	nerating	Tem	purature	Range:
u	peraurig	I CIII	purature	Nange.

-55.0/+125.0 degrees celsius

Storage Tempurature Range:

-65.0/+150.0 degrees celsius

End Application:

4920-00-216-9141

Features Provided:

Bipolar and high speed and high reliability and low current and high current and schottky and electrically alterable and programmed

Inclosure Material:

Ceramic

Inclosure Configuration:

Dual-in-line

Current Rating Per Characteristic:

-30.00 milliamperes collector cutoff current, dc, with specified resistance between base and emitter microamperes and 5.00 milliamperes reverse current, dc microamperes

Terminal Surface Treatment:

Solder

Product Name:

Microcircuit memory, 512 x 4 bit bipolar prom

Voltage Rating And Type Per Characteristic:

-0.5 volts total supply and 7.0 volts total supply

Time Rating Per Chacteristic:

40.00 nanoseconds af output megawatts

Memory Device Type:

Eeprom

Hybrid Technology Type:

Monolithic

Test Data Document:

81349-mil-i-43553 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.). And 96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.). And 96906-mil-std-130 standard (includes industry or association standards, individual manufactureer standards, etc.).

Terminal Type And Quantity:

16 printed circuit

Purchase Description Identification:

S7040-mc8304424-0

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

Yes - demil/mli

Fiig:

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